## General Description

FSMOS® MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The low $V_{th}$ series is specially optimized for synchronous rectification systems with low driving voltage.

## Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

## Applications

- Switching mode power supply
- Motor driver
- Battery protection
- DC-DC convertor
- Inverter
- UPS

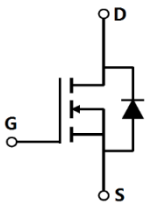
## Key Performance Parameters

| Parameter | Value | Unit |
|---|---|---|
| $V_{DS}$ | 80 | V |
| $I_{D, pulse}$ | 520 | A |
| $R_{DS(ON), max}$ @ $V_{GS}$=10V | 2.4 | mΩ |
| $Q_g$ | 73.8 | nC |

## Marking Information

| Product Name | Package | Marking |
|---|---|---|
| SFS08R024UGF | PDFN5x6 | SFS08R024UG |

## Package & Pin information

## Absolute Maximum Ratings at $T_j$=25°C unless otherwise noted

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Drain-source voltage | $V_{DS}$ | 80 | V |
| Gate-source voltage | $V_{GS}$ | ±20 | V |
| Continuous drain current[1], $T_C$=25 °C | $I_D$ | 130 | A |
| Pulsed drain current[2], $T_C$=25 °C | $I_{D, pulse}$ | 520 | A |
| Continuous diode forward current[1], $T_C$=25 °C | $I_S$ | 130 | A |
| Diode pulsed current[2], $T_C$=25 °C | $I_{S, pulse}$ | 520 | A |
| Power dissipation[3], $T_C$=25 °C | $P_D$ | 132 | W |
| Single pulsed avalanche energy[5] | $E_{AS}$ | 205 | mJ |
| Operation and storage temperature | $T_{stg}$, $T_j$ | -55 to 175 | °C |

## Thermal Characteristics

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Thermal resistance, junction-case | $R_{\theta JC}$ | 1.14 | °C/W |
| Thermal resistance, junction-ambient[4] | $R_{\theta JA}$ | 62 | °C/W |

## Electrical Characteristics at $T_j$=25°C unless otherwise specified

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test condition |
|---|---|---|---|---|---|---|
| Drain-source breakdown voltage | $BV_{DSS}$ | 80 | | | V | $V_{GS}$=0 V, $I_D$=250 μA |
| Gate threshold voltage | $V_{GS(th)}$ | 1 | | 2.5 | V | $V_{DS}$=$V_{GS}$, $I_D$=250 μA |
| Drain-source on-state resistance | $R_{DS(ON)}$ | | 2 | 2.4 | mΩ | $V_{GS}$=10 V, $I_D$=50 A |
| | | | 2.7 | 3.5 | | $V_{GS}$=4.5 V, $I_D$=50 A |
| Gate-source leakage current | $I_{GSS}$ | | | 100 | nA | $V_{GS}$=20 V |
| | | | | -100 | | $V_{GS}$=-20 V |
| Drain-source leakage current | $I_{DSS}$ | | | 1 | uA | $V_{DS}$=80 V, $V_{GS}$=0 V |
| Gate resistance | $R_G$ | | 2.8 | | Ω | $f$=1 MHz, Open drain |

## Dynamic Characteristics

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test condition |
|---|---|---|---|---|---|---|
| Input capacitance | $C_{iss}$ | | 4850 | | pF | $V_{GS}$=0 V, $V_{DS}$=25 V, $f$=100 kHz |
| Output capacitance | $C_{oss}$ | | 1950 | | pF | |
| Reverse transfer capacitance | $C_{rss}$ | | 116 | | pF | |
| Turn-on delay time | $t_{d(on)}$ | | 13 | | ns | $V_{GS}$=10 V, $V_{DS}$=40 V, $R_G$=2 Ω, $I_D$=40 A |
| Rise time | $t_r$ | | 11 | | ns | |
| Turn-off delay time | $t_{d(off)}$ | | 59 | | ns | |
| Fall time | $t_f$ | | 22 | | ns | |

## Gate Charge Characteristics

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test condition |
|---|---|---|---|---|---|---|
| Total gate charge | $Q_g$ | | 73.8 | | nC | $V_{GS}$=10 V, $V_{DS}$=40 V, $I_D$=40 A |
| Gate-source charge | $Q_{gs}$ | | 12.4 | | nC | |
| Gate-drain charge | $Q_{gd}$ | | 12 | | nC | |
| Gate plateau voltage | $V_{plateau}$ | | 3 | | V | |

## Body Diode Characteristics

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test condition |
|---|---|---|---|---|---|---|
| Diode forward voltage | $V_{SD}$ | | | 1.3 | V | $I_S$=12 A, $V_{GS}$=0 V |
| Reverse recovery time | $t_{rr}$ | | 70 | | ns | $V_R$=40 V, $I_S$=40 A, di/dt=100 A/μs |
| Reverse recovery charge | $Q_{rr}$ | | 66 | | nC | |
| Peak reverse recovery current | $I_{rrm}$ | | 1.6 | | A | |

**Note**

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in$^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_a$=25 °C.
5) $V_{DD}$=50 V,$V_{GS}$=10 V, L=0.3 mH, starting $T_j$=25 °C.

## Electrical Characteristics Diagrams

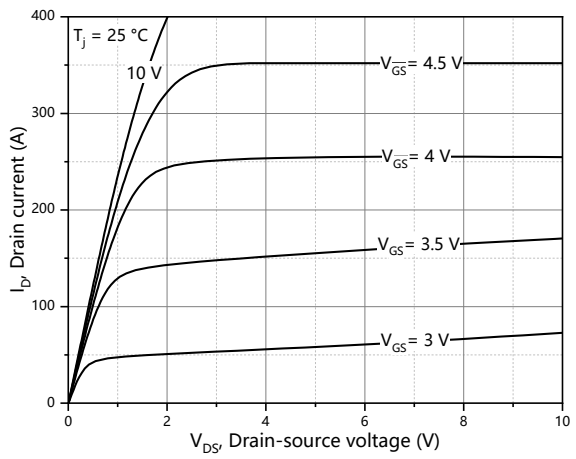



**Figure 1. Typ. output characteristics**

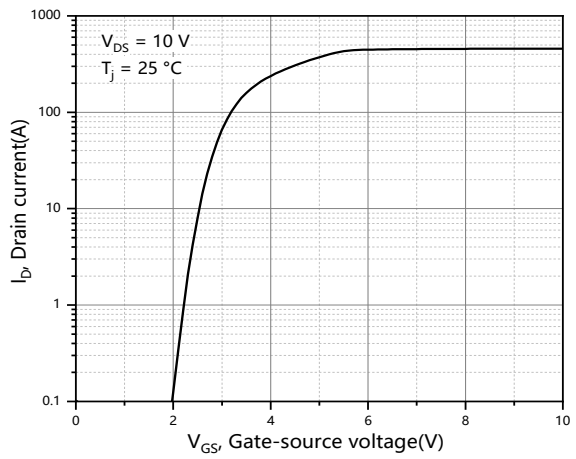



**Figure 2. Typ. transfer characteristics**

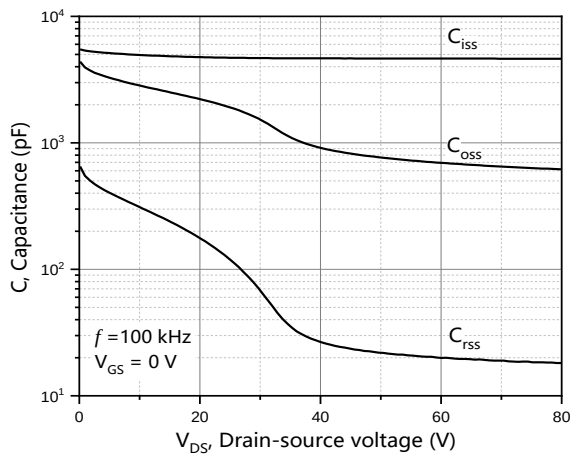



**Figure 3. Typ. capacitances**

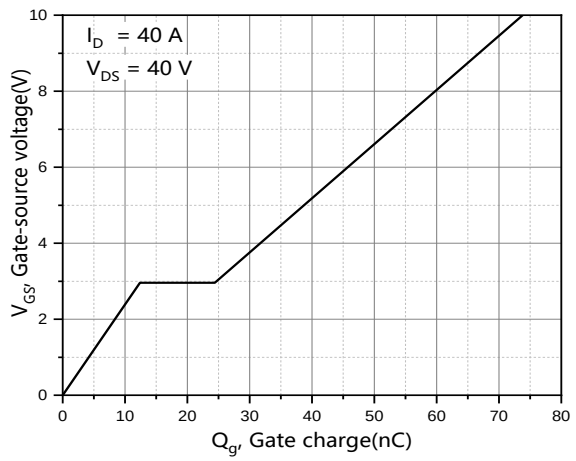



**Figure 4. Typ. gate charge**

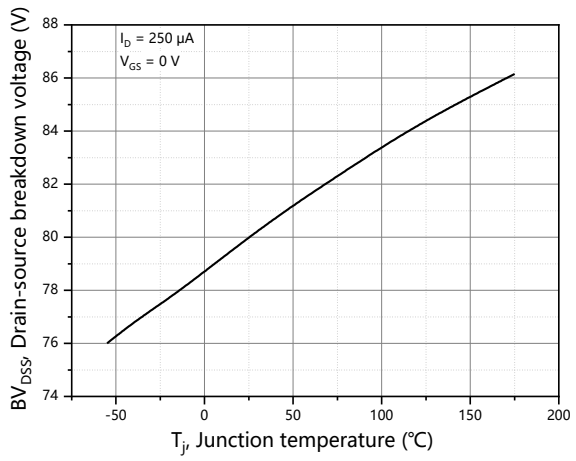



**Figure 5. Drain-source breakdown voltage**

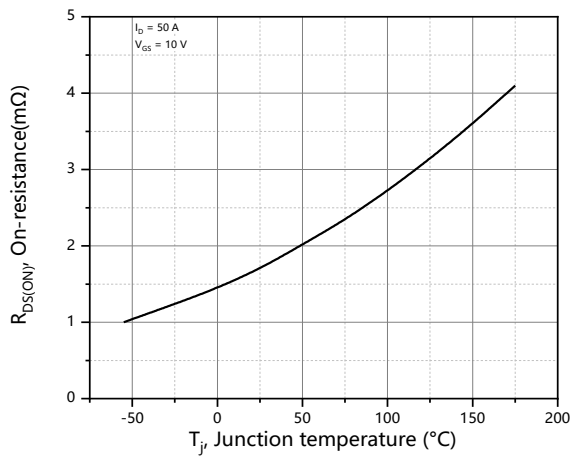



**Figure 6. Drain-source on-state resistance**

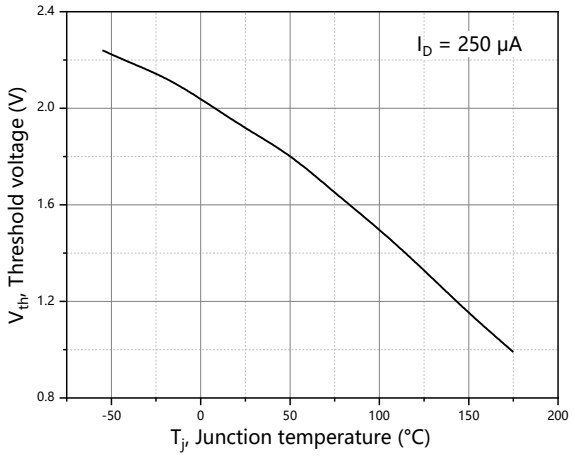



**Figure 7. Threshold voltage**

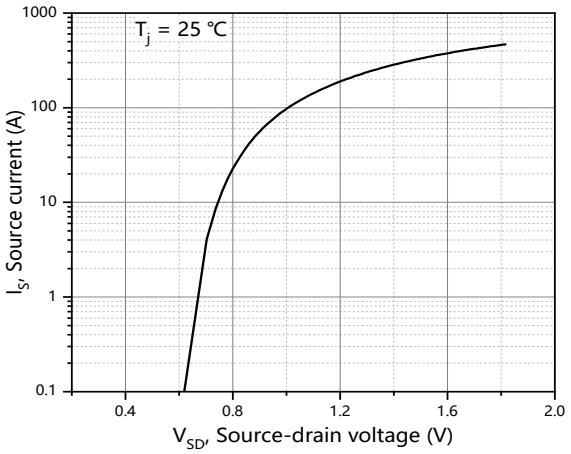



**Figure 8. Forward characteristic of body diode**

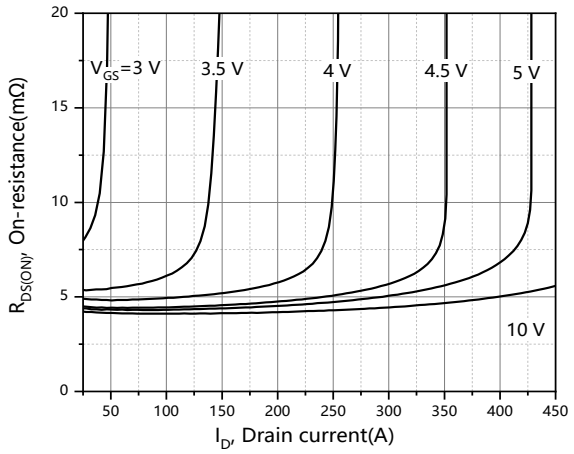



**Figure 9. Drain-source on-state resistance**

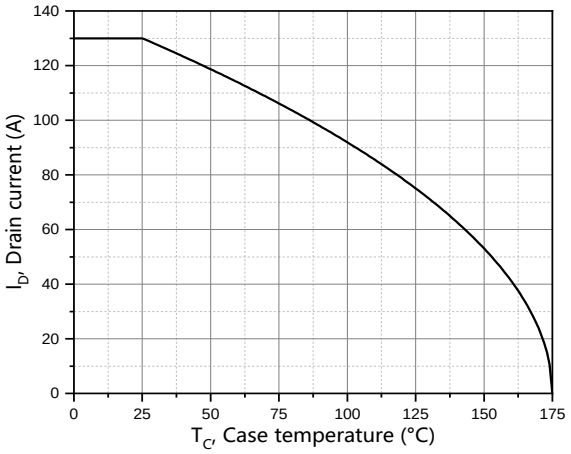



**Figure 10. Drain current**

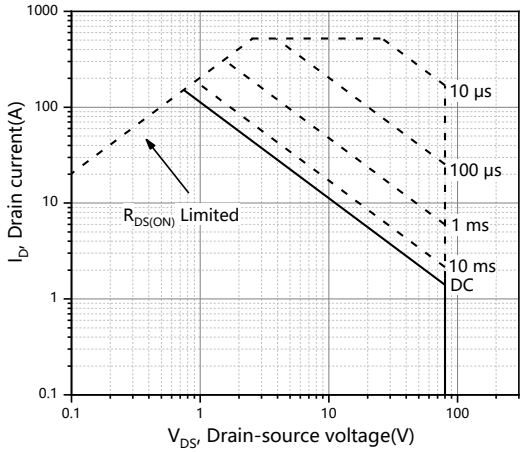



**Figure 11. Safe operation area $T_C$=25 ℃**

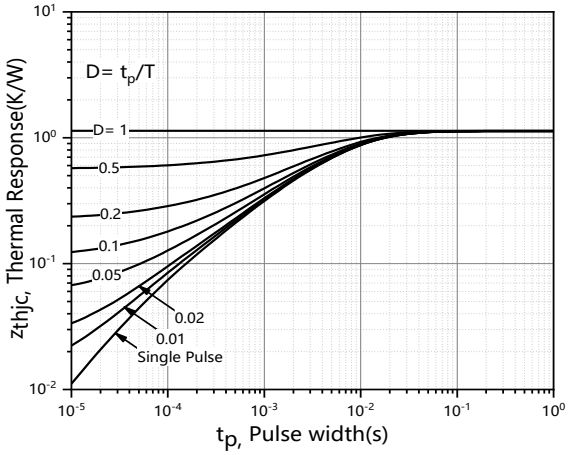



**Figure 12. Max. transient thermal impedance**

## Test circuits and waveforms

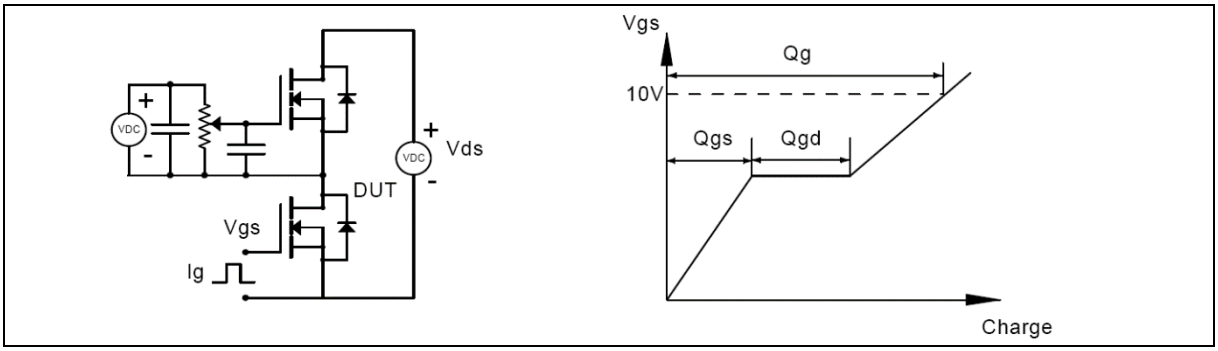



**Figure 1. Gate charge test circuit & waveform**

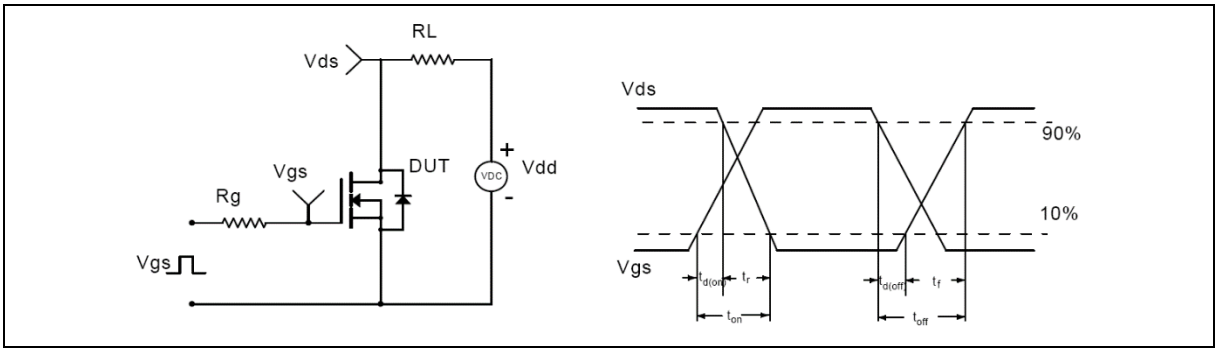



**Figure 2. Switching time test circuit & waveforms**

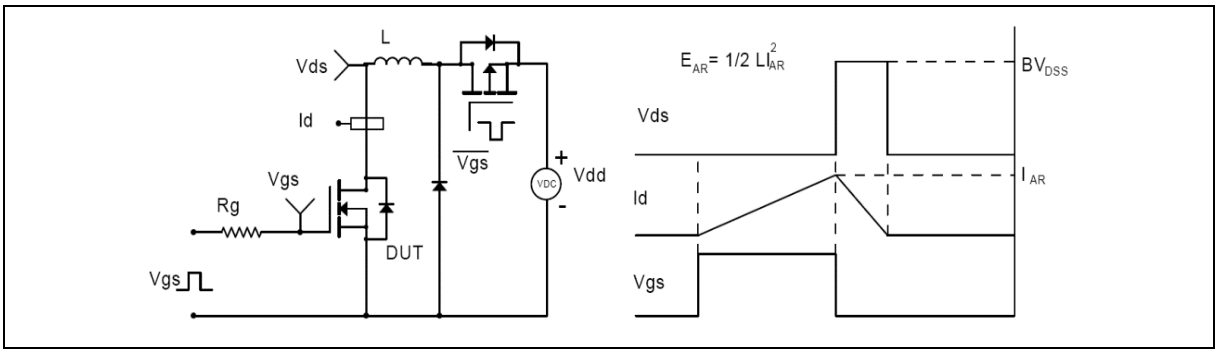



**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**

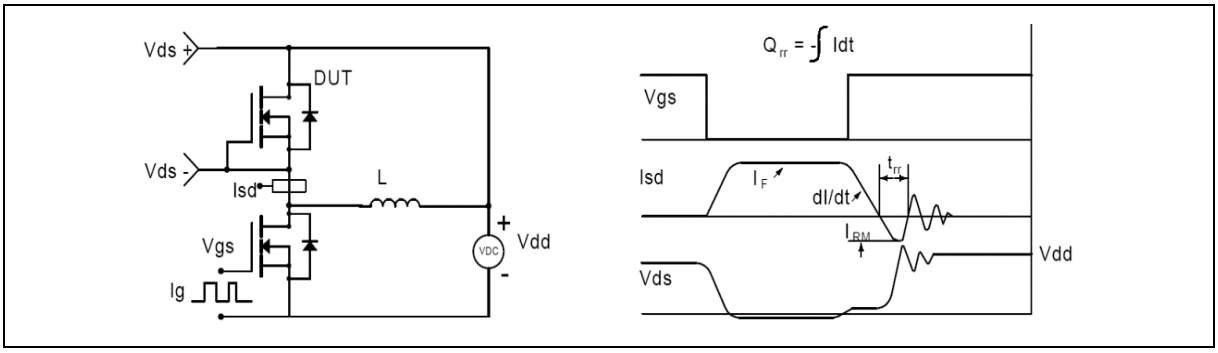
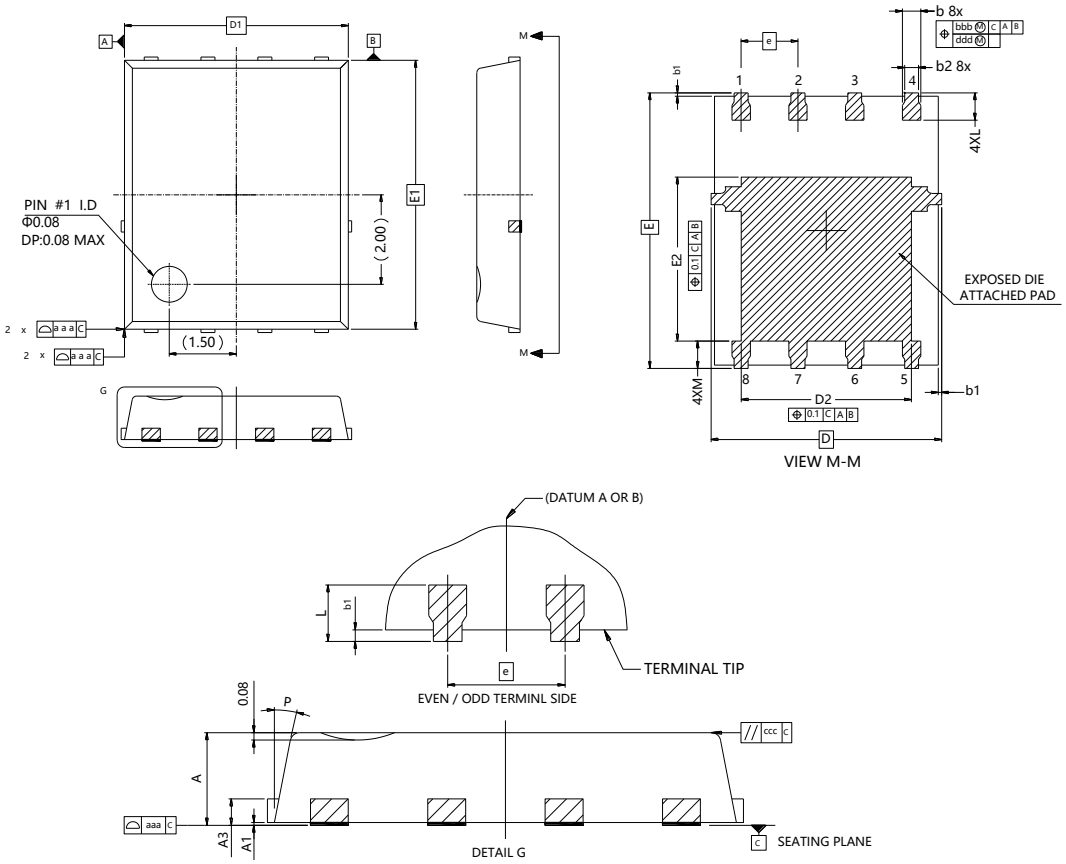



**Figure 4. Diode reverse recovery test circuit & waveforms**

## Package Information




| Symbol | mm | |
|---|---|---|
| | Min | Max |
| A | 0.95 | 1.05 |
| A1 | 0.00 | 0.05 |
| A3 | 0.25 REF | |
| b | 0.31 | 0.51 |
| b1 | 0.03 | 0.13 |
| b2 | 0.21 | 0.41 |
| D | 5.15 BSC | |
| D1 | 5.00 BSC | |
| D2 | 3.70 | 3.90 |
| E | 6.15 BSC | |
| E1 | 6.00 BSC | |
| E2 | 3.56 | 3.76 |
| e | 1.27 BSC | |
| L | 0.51 | 0.71 |
| M | 0.51 | 0.71 |
| P | 10° | 12° |

Version 1: PDFN5x6-S package outline dimension

## Ordering Information

| Package Type | Units/ Reel | Reels/ Inner Box | Units/ Inner Box | Inner Boxes/ Carton Box | Units/ Carton Box |
|---|---|---|---|---|---|
| PDFN5x6-S | 5000 | 1 | 5000 | 10 | 50000 |

## Product Information

| Product | Package | Pb Free | RoHS | Halogen Free |
|---|---|---|---|---|
| SFS08R024UGF | PDFN5x6 | yes | yes | yes |

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